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Ferechteh Hosseini Teherani
David C. Look
Cole W. Litton
David J. Rogers
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In Memoriam

Cole W. Litton

Sept. 29, 1930 – Jan. 26, 2010

These proceedings are dedicated to the memory of Dr. Cole Litton, who passed away while attending the Photonics West 2010 symposium. The oxide semiconductor community will forever be indebted to Cole for his enthusiasm, kindness and tireless efforts to promote research into zinc oxide for optoelectronics applications.